Dr.P.SUVEETHA DHANASELVAM, M.E, Ph.D.,
Associate Professor, ECE
Velammal College of Engineering and Technology, Madurai
psd@vcet.ac.in

Educational Qualification:

S.No	Name of the Degree	Institution/ University	Area of Specialization	Year Of passing	Class Obtained
1.	Ph.D	Anna University, Chennai	VLSI	2014	Highly Commended
2.	M.E	Sathyabama Institute of Science and Technology,Chennai	Applied Electronics	2006	First class with Distinction
3.	B.E	St.Peter's Engineering College,Chennai	ECE	2001	First class with Distinction

Experience in Years: 18 years

Employment History:

S.No	Name of the College/Industry	Designation	Period		Year of Service
			From	To	
1.	Velammal College of Engineering and Technology,Madurai	Associate Professor	May 2014	Till date	8 years 2 months
		Assistant Professor	June 2009	April 2014	5 years
2.	Sacs M.A.V.M.M. Engineering College	Senior Lecturer	June 2006	April 2009	3 years
3.	PandiyanSaraswathi Yadav Engineering College	Lecturer	June 2002	April 2003	1 year
4.	Tagore Engineering College,Chennai	Lecturer	August 2001	May 2002	10 months

Interested Research Areas: VLSI, Signal Processing, Cryptography

Scholarships and Awards received:

TARE(Teachers Associateship for Research Excellence award) from SERB, DST

Funded Research Projects:

S.No	Funding Agency	Title	Sanctioned Amount	Year	PI/Co-PI
1.	SERB-TARE	PerformanceAnalysis andCharacterizationof Si/ZnOHeterojunctionDiode as Pressure Sensor	Rs.18.30 Lakhs	2018-2022	PI
2.	ICPS,DST	DigitalReconstruction ofPoompuhar	Rs.30 Lakhs	2019-2021	Co-PI

Patent rights received:

"A Multi layer Gate Metal Oxide Semiconductor FET for reducing short channel effect"

- Patent published online on 29-5-2020

Publications Details:

Books:

1. "Analytical Modeling and Simulation of TMSG MOSFETs"- Lambert Academic Publishing

2. "VLSI Design" ShanlaxPublishers

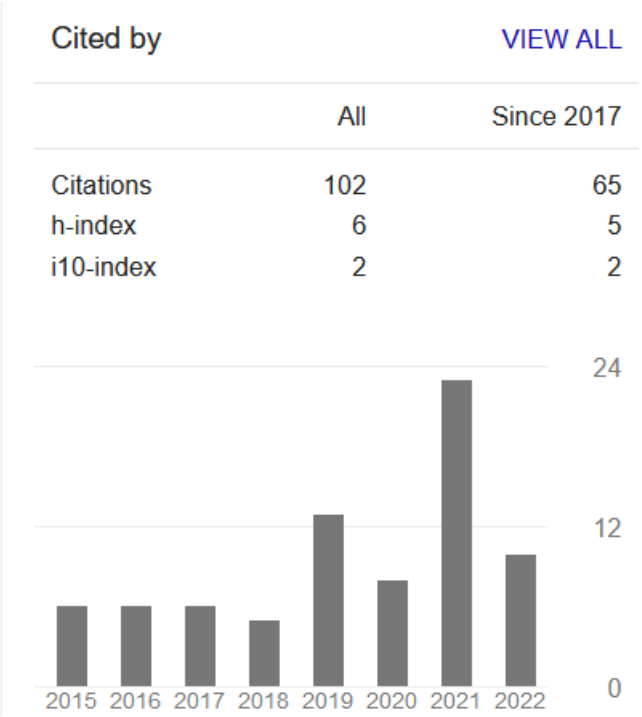
Conference Papers: 42

Journal Publications:17

S.No.	Title of the paper	Journal	Year of Publication
1.	Analytical Approach Of A Nanoscale Triple-Material Surrounding Gate Mosfets For Reduced Short Channel Effects	Elsevier-Microelectronics Journal	2013
2.	A 2D Transconductance And Sub-Threshold Behavior Model For Triple Material Surrounding Gate Mosfets	Elsevier-Microelectronics Journal	2013
3.	A 2D SubthresholdCurrent Model Single Halo Triple Material Surrounding Gate (SHTMSG) MOSFET	Elsevier-Microelectronics Journal	2014
4.	A 2D Analytical Modeling Of Single Halo Triple Material Surrounding Gate (SHTMSG) MOSFET	Journal of Electrical Engineering and Technology	2014

5.	Performance analysis of fully depleted triple material surrounding gate (TMSG) MOSFET	Journal of Computational Electronics, Springer	2014
6.	Analytical Modelling of Surface Potential in Dual Material Junctionless Surrounding Gate MOSFET	International Journal of Innovative Research in Science, Engineering and Technology	2014
7.	Analytical Modelling of ElectricField Distribution in DualMaterial Junction lessSurrounding Gate MOSFET	International Journal of VLSIDesign and CommunicationSystem	2014
8.	Real time Encryption and Decryption using Blowfish algorithm	International Journal of Emerging Technology in Computer Science and Electronics.	2016
9.	Real Time Implementation of RecursiveKaratsuba Algorithm Using VLSI	International Journal of Innovative Research in Computer and Communication Engineering	2016
10.	The Vibe Stick -A Modular Cane Stick for the Blind	International journal on Organization of Science and Innovative Engineering & Technology	2016
11.	A Survey on features of Sound Signal	Journal of Applied Science and Computations	2018
12.	A 2D Analytical Modeling and Simulation of Double Halo Triple MaterialSurrounding Gate (DH-TMSG) MOSFET	Silicon, Springer	2020
13.	A 2D Unified Subthreshold Drain Current Investigation for Junctionless Cylindrical Surrounding Gate(JCSG) Silicon Nanowire Transistor	Silicon, Springer	2020
14.	Pressure Sensors Using Si/ZnO Heterojunction Diode	Silicon, Springer	2021
15.	A Quasi 2-D Electrostatic Potential and Threshold Voltage Model for Junctionless Triple Material Cylindrical Surrounding Gate Si Nanowire Transistor	Journal of Nanoelectronics and Optoelectronics 16(2):318-323	2021
16.	Analytical Modeling and Simulation Based Investigation of Triple Material Surrounding Gate Heterojunction Tunnel FET	Silicon, Springer	Accepted for Publication
17.	Neonatal cry signal prediction and classification via dense convolution neural network	Journal of Intelligent & Fuzzy Systems	Accepted for Publication

Google Scholar Report:



Other Profile:

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